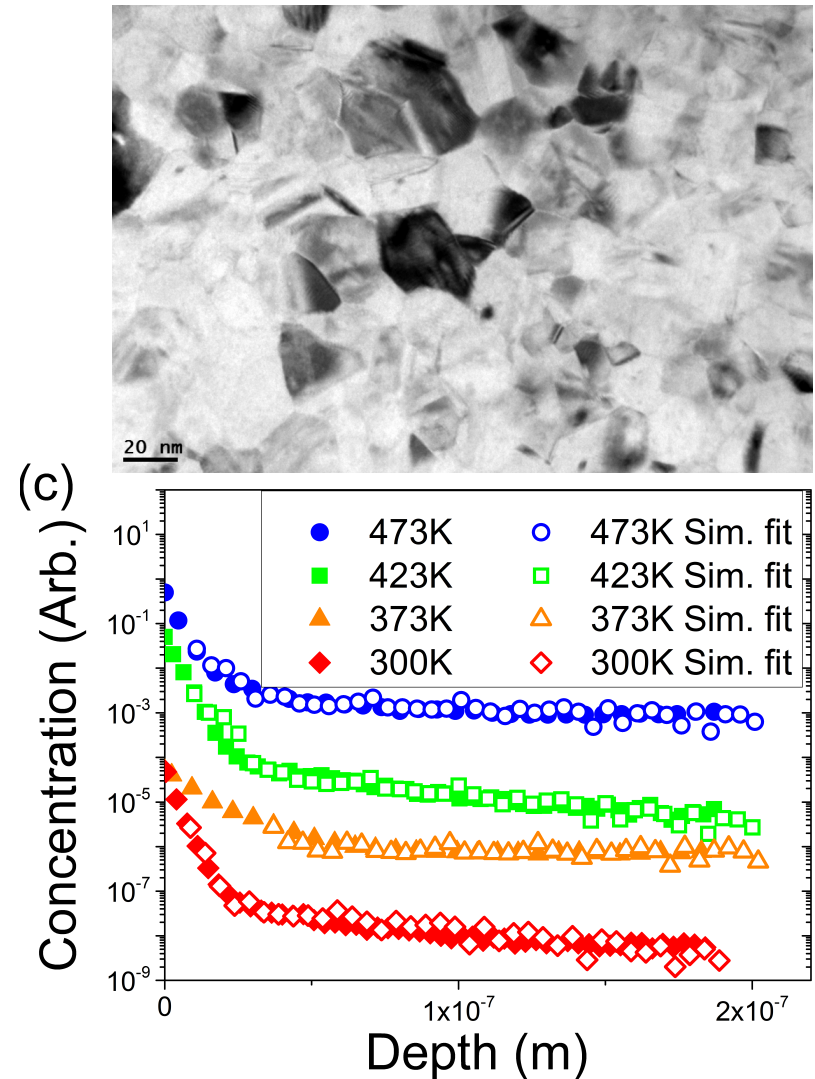
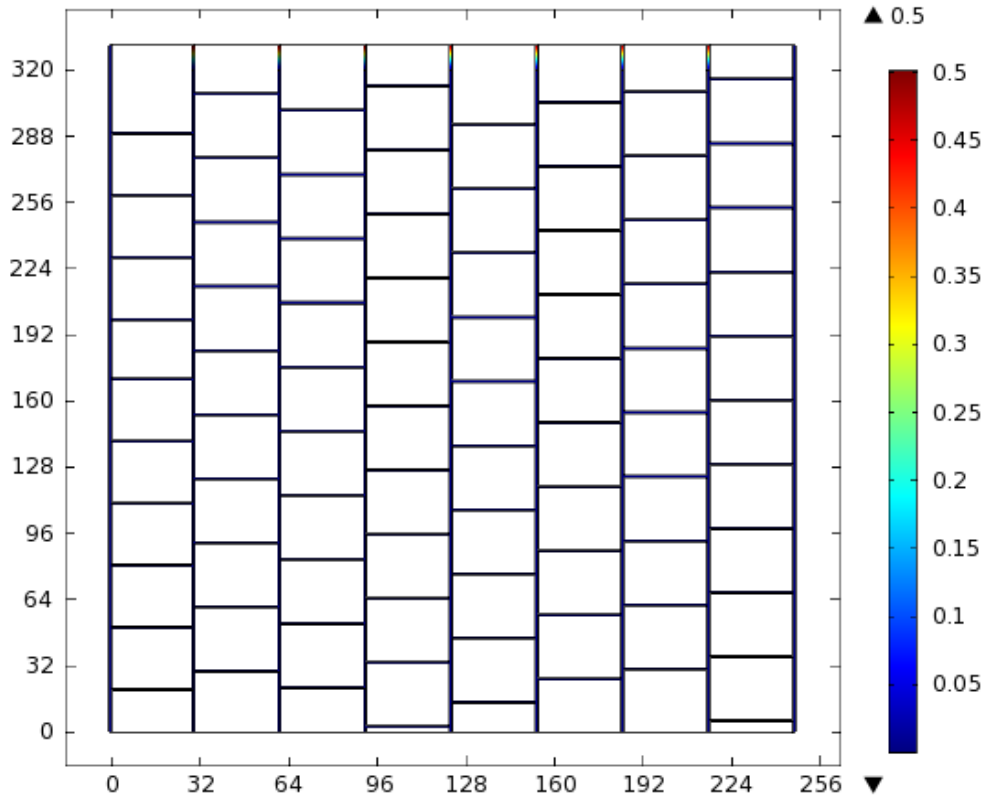


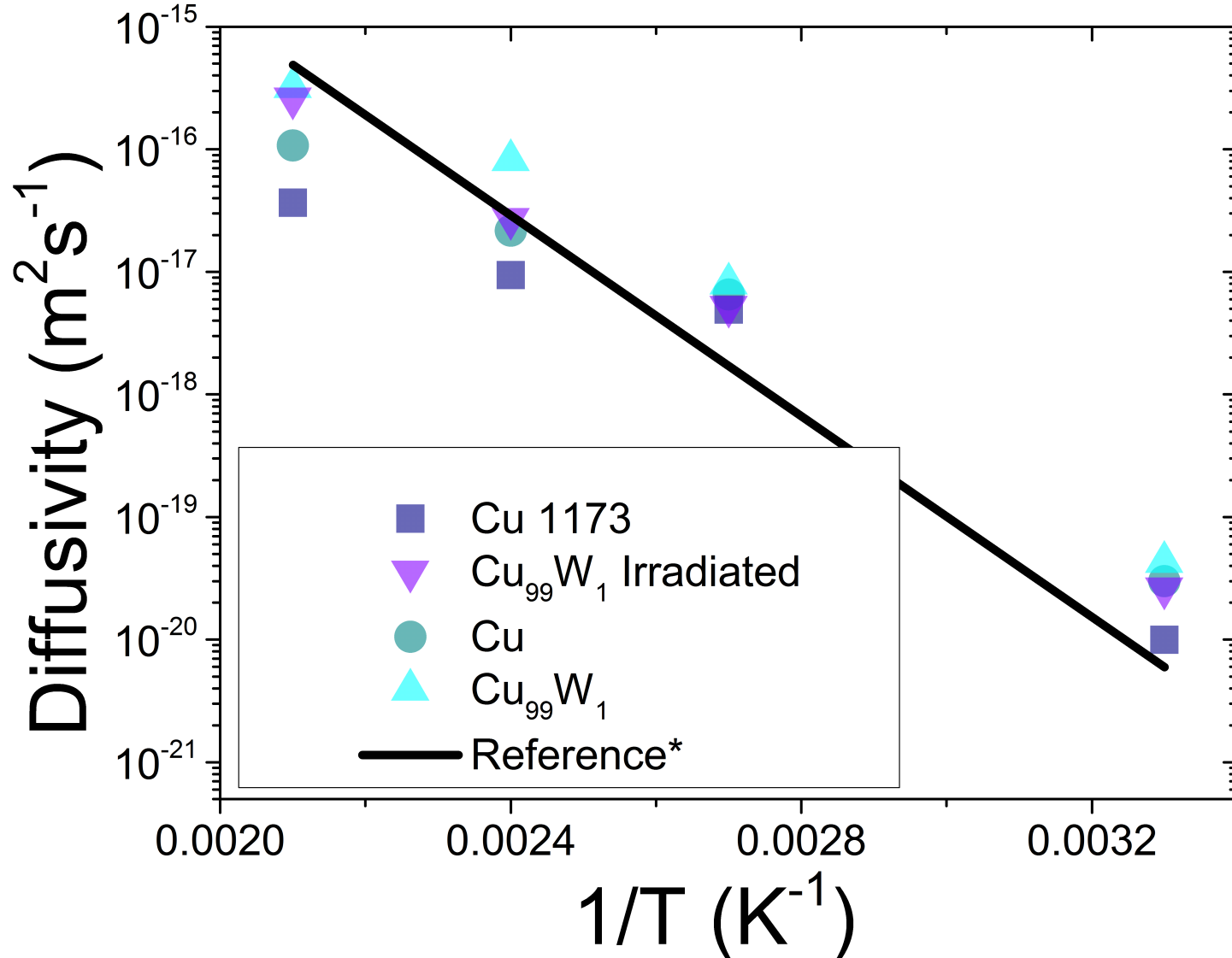
Finite Element Simulation

Grain boundary diffusion in thin film model:

Near surface ($10\sim 20\text{nm}$) D_{sb} different from D_b in film



Results of Au G.B. Diffusion in Cu

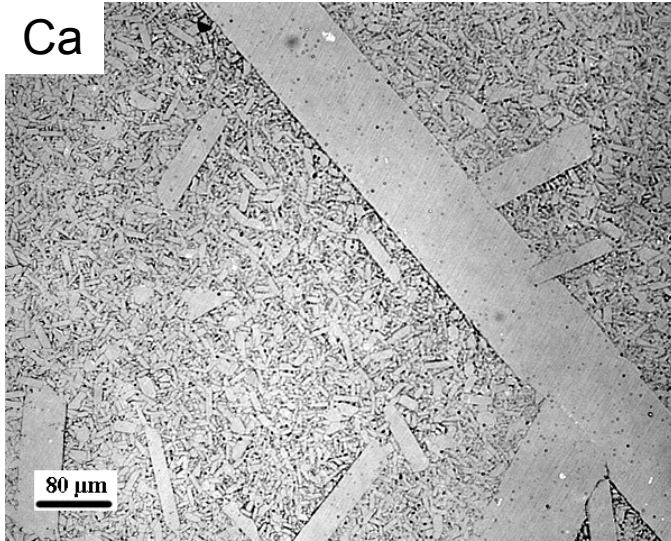


Au diffusivity in the Cu – Limited ‘nano-effect’

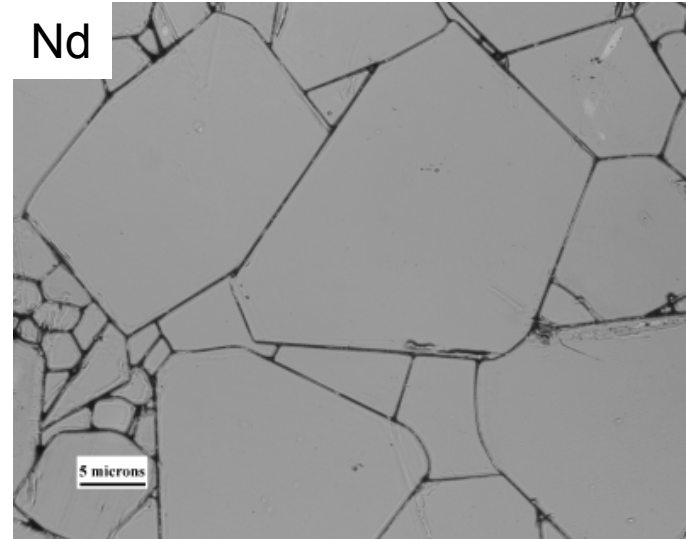
*Ref. Surholt, Mishin, Herzig, *Phys. Rev. B* (1994).

Aluminum Oxide

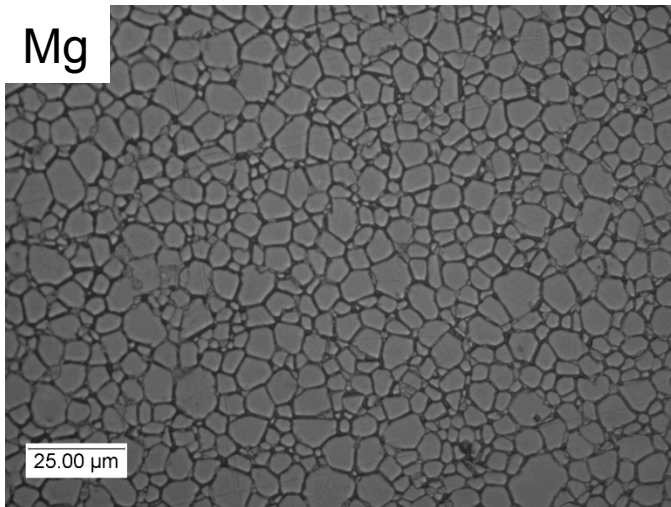
Ca



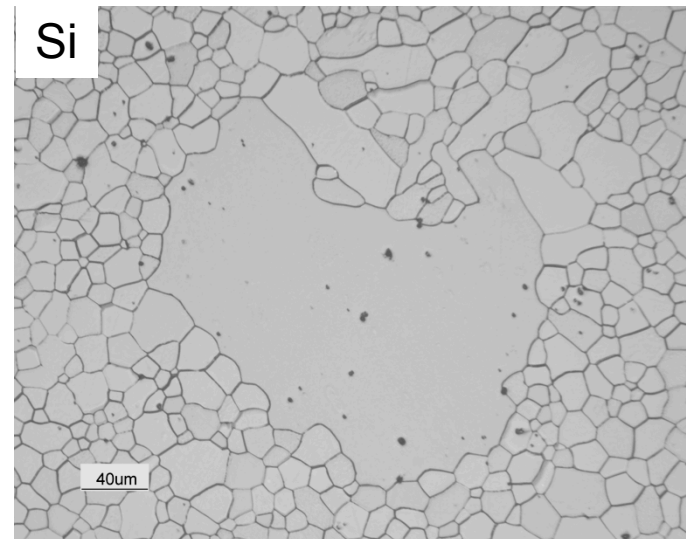
Nd



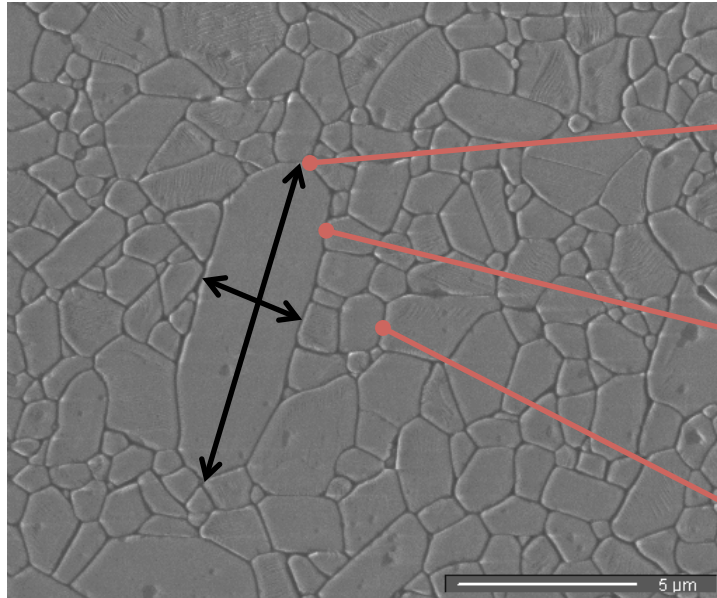
Mg



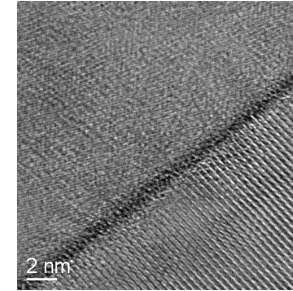
Si



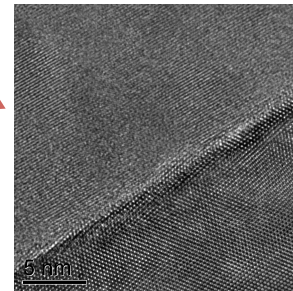
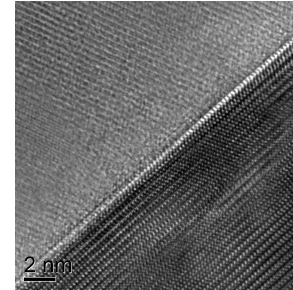
Experimental Approach



Quench



Quench



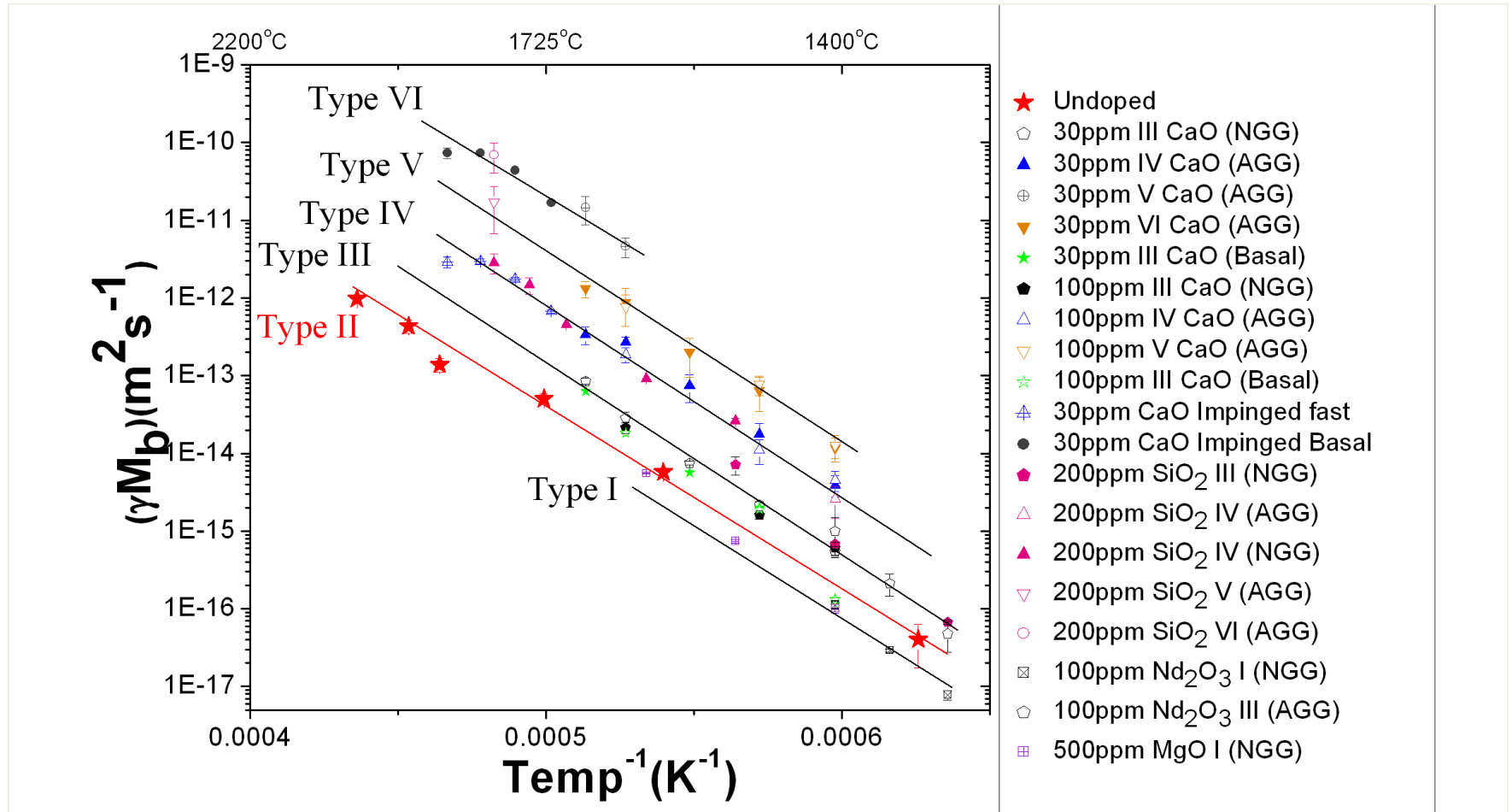
TEM

Compositions Investigated

- Calcia-doped Alumina (30, 100, 500 ppm)
- Silica-doped Alumina (200, 500 ppm)
- Magnesia-doped Alumina (500 ppm)
- Neodymia-doped Alumina (100 ppm)

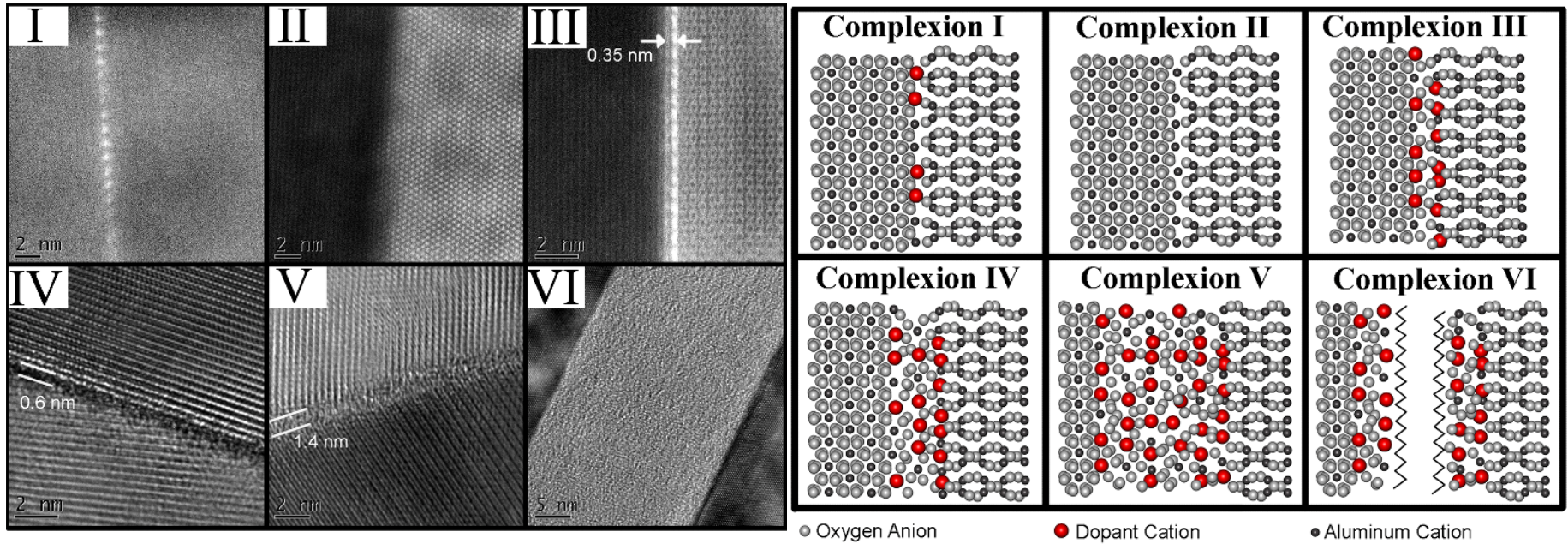
Wide Temperature Range: 1300-2020°C

Grain Growth Kinetic Types

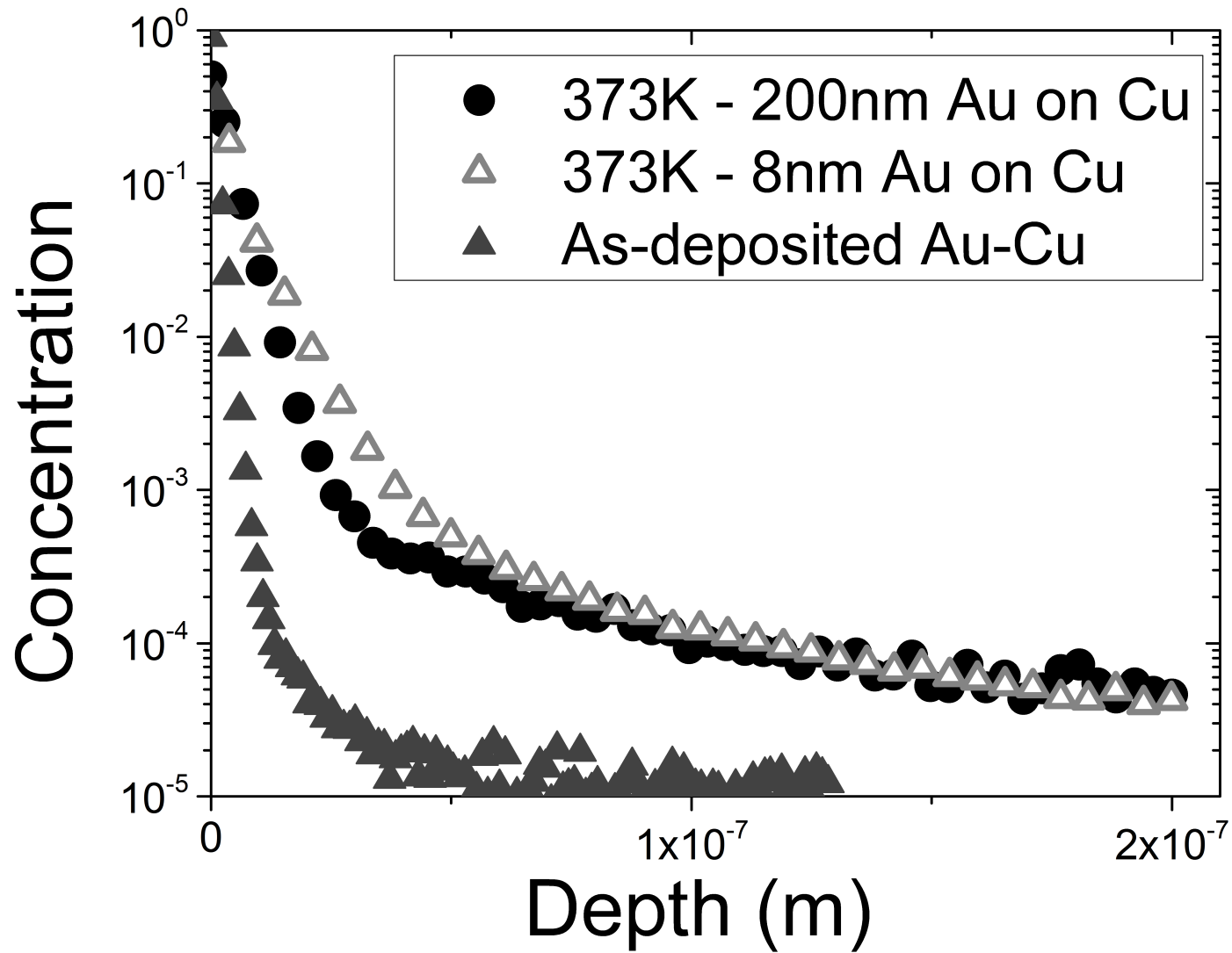


S.J. Dillon, M. Tang, W.C. Carter, M.P. Harmer, "Complexion: A new concept for kinetic engineering in materials science," *Acta Mater.* 55[18] 6208-6218 (2007)

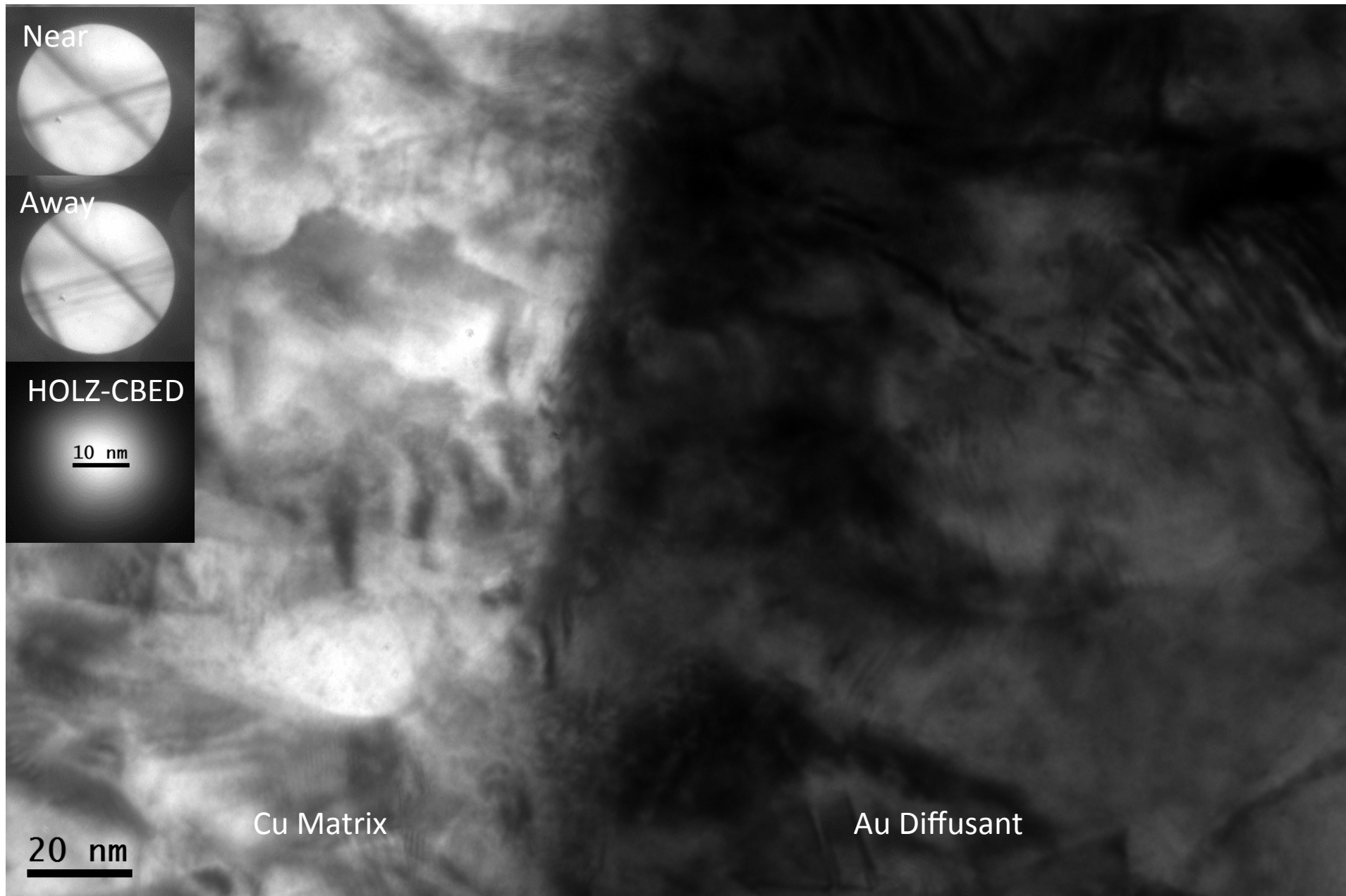
Nanoscale Interface Structure



Variation in structure on nano-scale can produce orders of magnitude changes in properties



Stress at Interface



Model for Equiaxed Nanograins

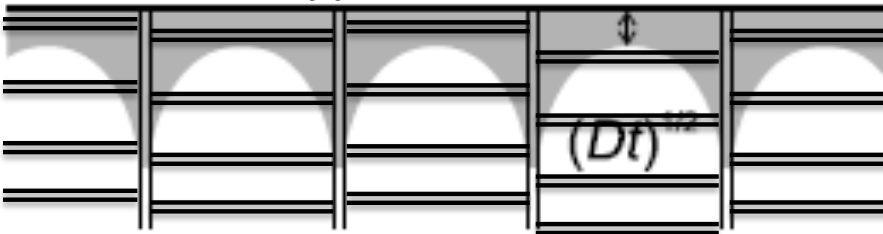
Type B



Constant Source

$$sD_{gb}\delta = 1.308\sqrt{\frac{D}{t}}(-\partial\bar{c}/\partial z^{6/5})^{-5/3}$$

Modified 'Type B'-like model



Constant Source

$$D_{gb}\delta = 1.308\sqrt{\frac{D^{eff}J}{t}}(-\partial\bar{c}/\partial z^{6/5})^{-5/3}$$

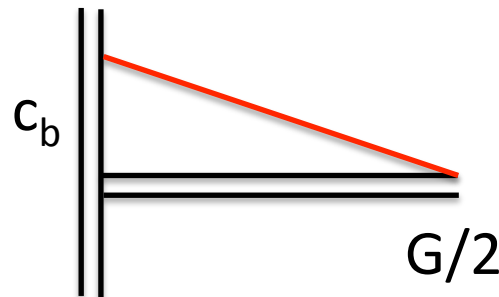
Correction Factor, J

Motivation – Basis of Type B

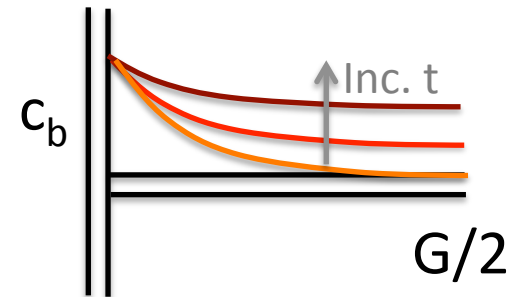
$$\frac{\partial c_b}{\partial t} = D_b \frac{\partial^2 c_b}{\partial x^2} - J \frac{2D}{\delta} \frac{\partial c_g}{\partial r} \Big|_{r=r_b}$$

$$J = \frac{\int D(\partial c / \partial x) dt}{\int D(\partial^2 c / \partial x^2) dt}$$

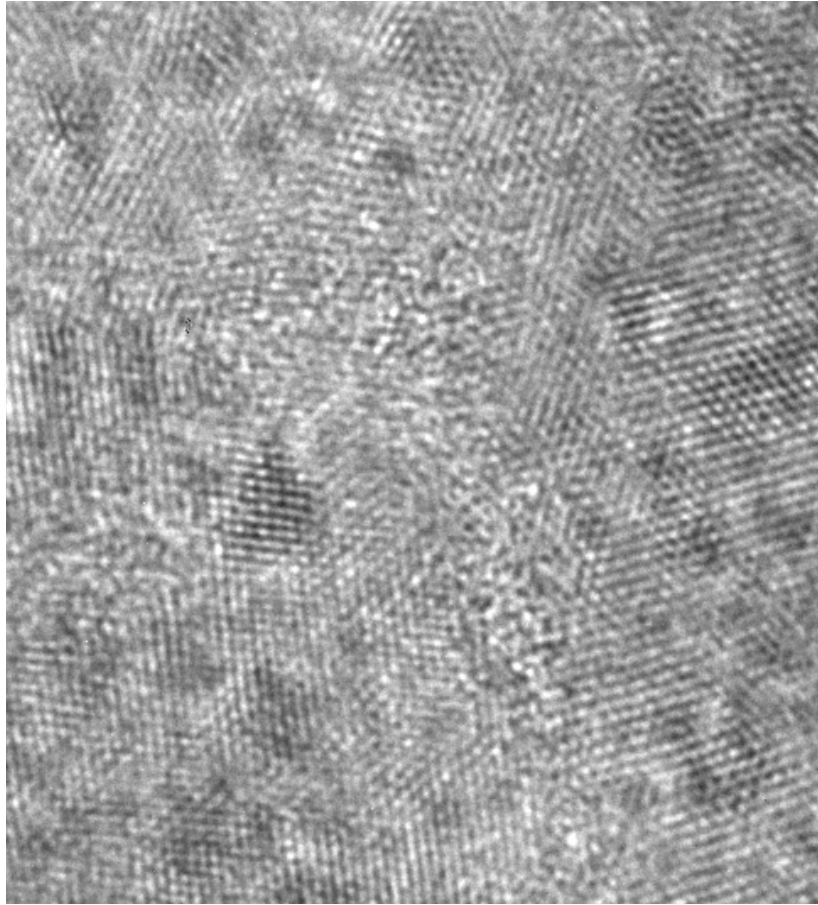
$$\partial c / \partial t = D(\partial c / \partial x)$$



$$\partial c / \partial t = D(\partial^2 c / \partial x^2)$$



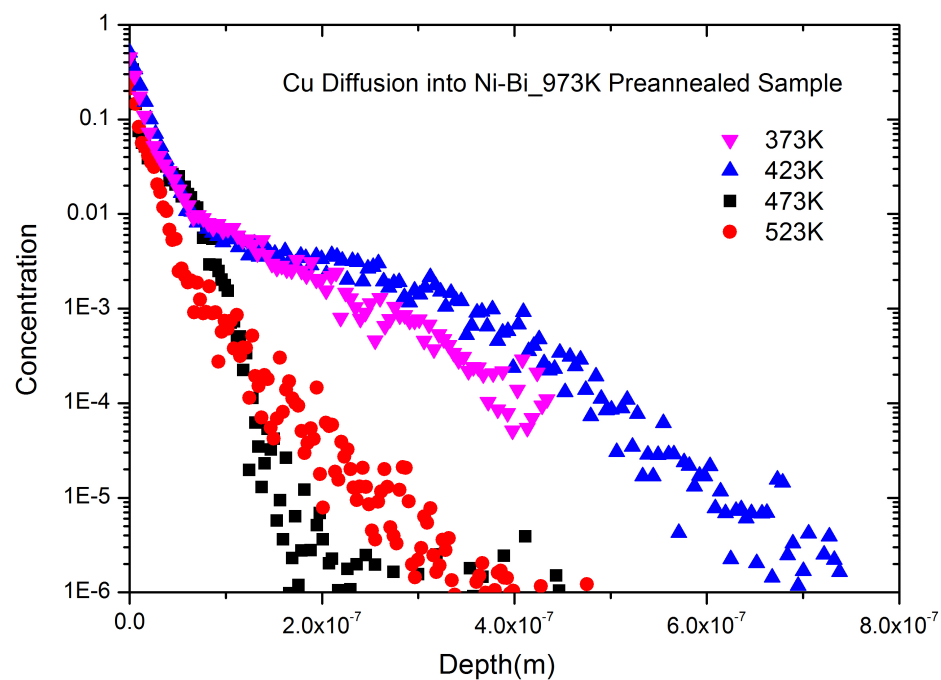
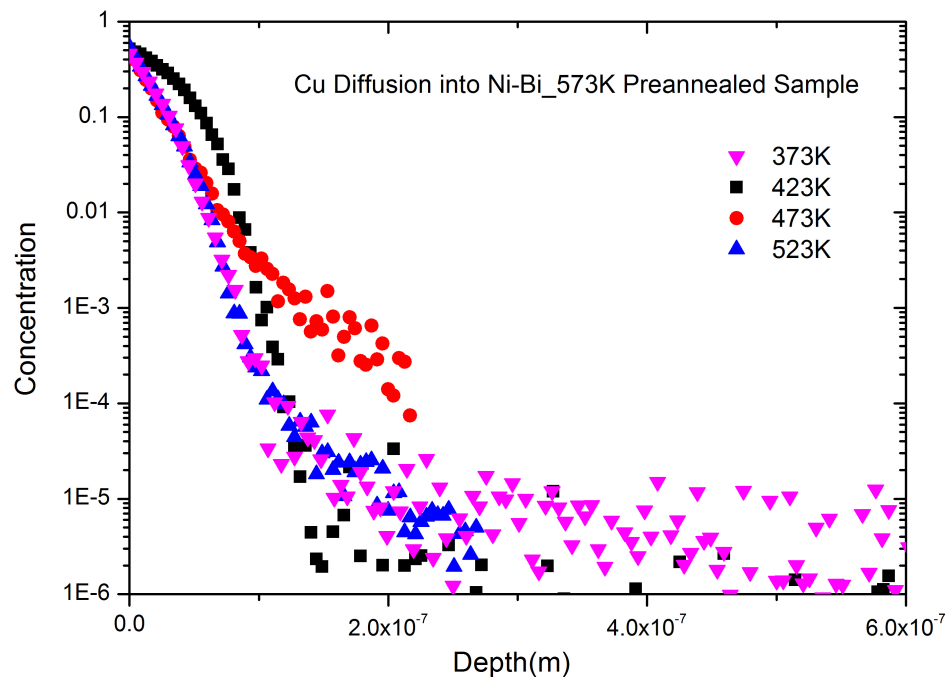
Disorder-Order Transition Irradiated Cu-W



Cu diffusion into Bi-doped Ni Matrix

Low T pre-anneal 300°C

High T pre-anneal 700°C

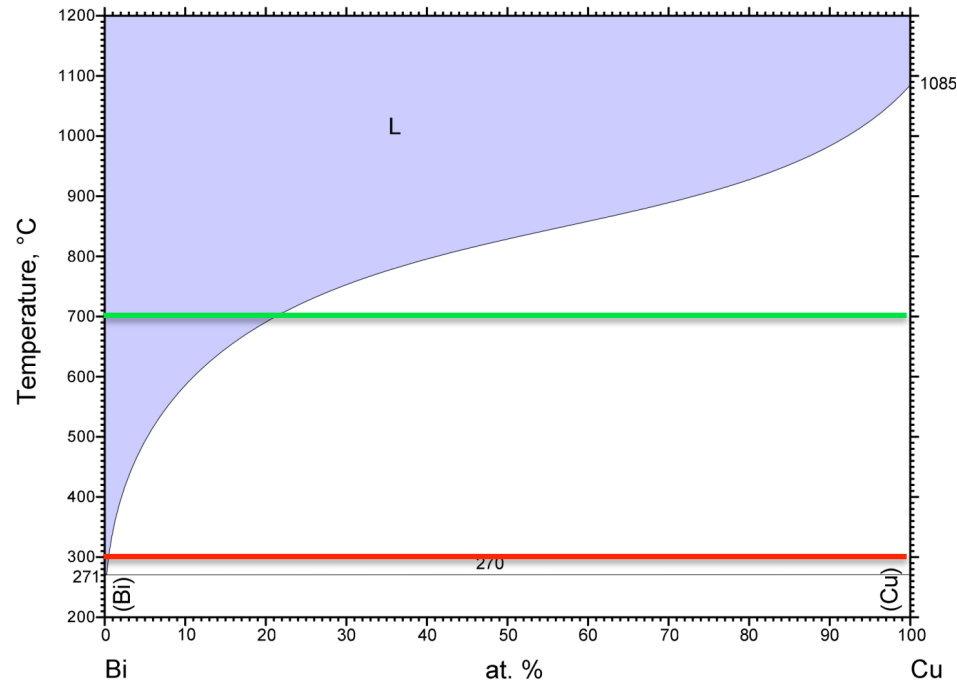
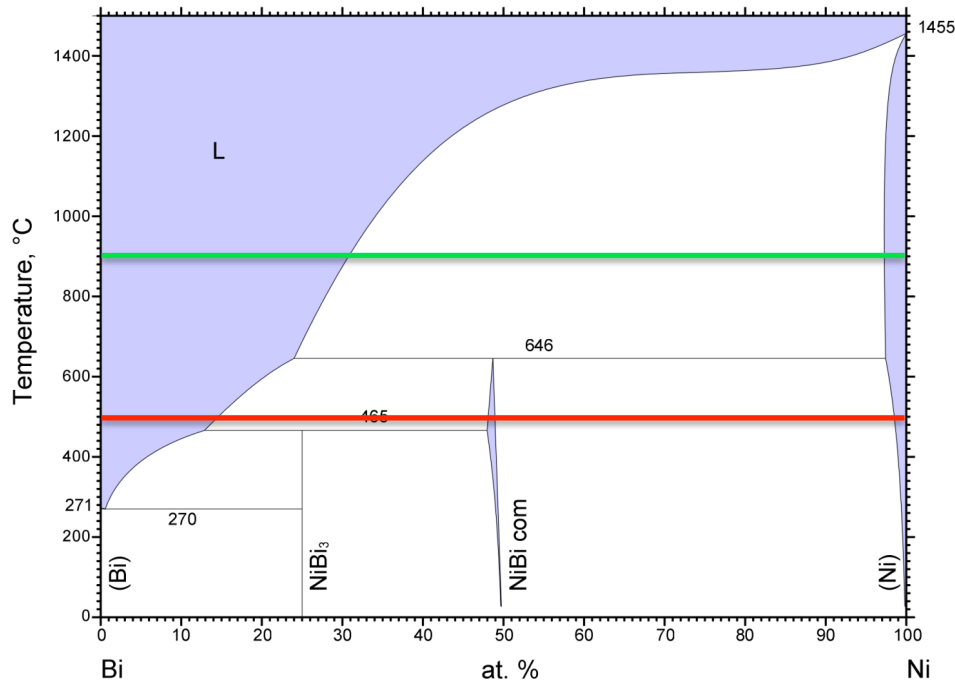


Comparison of 2 Model Systems

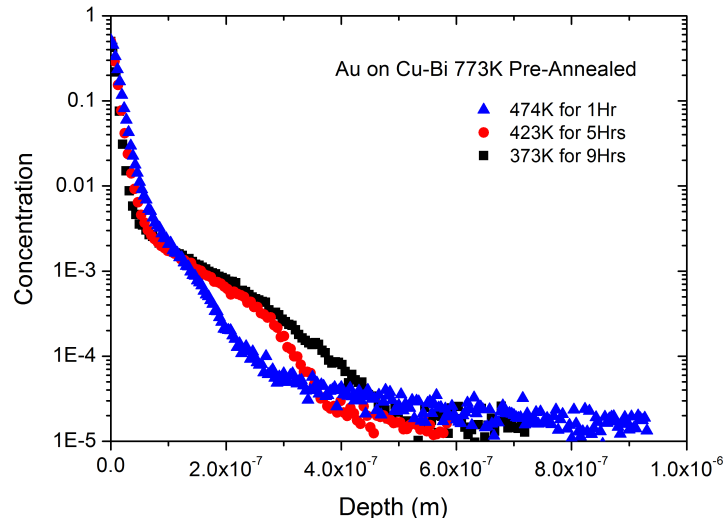
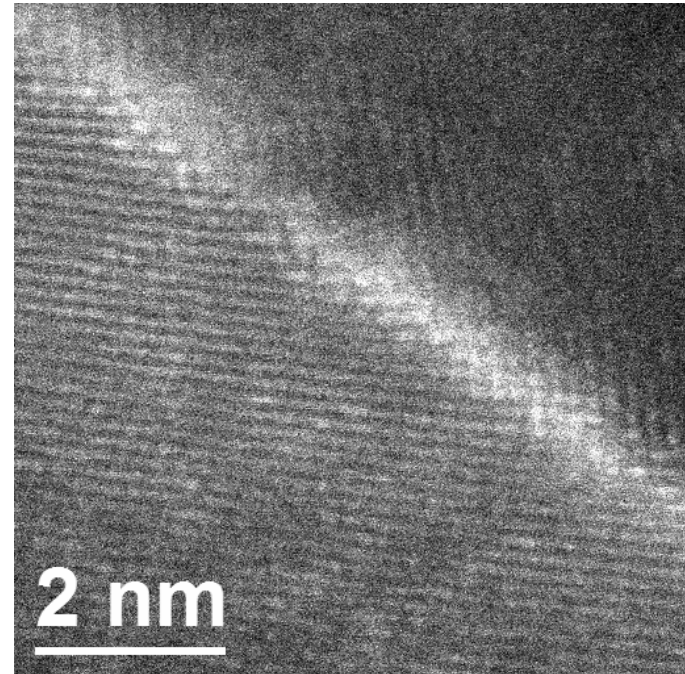
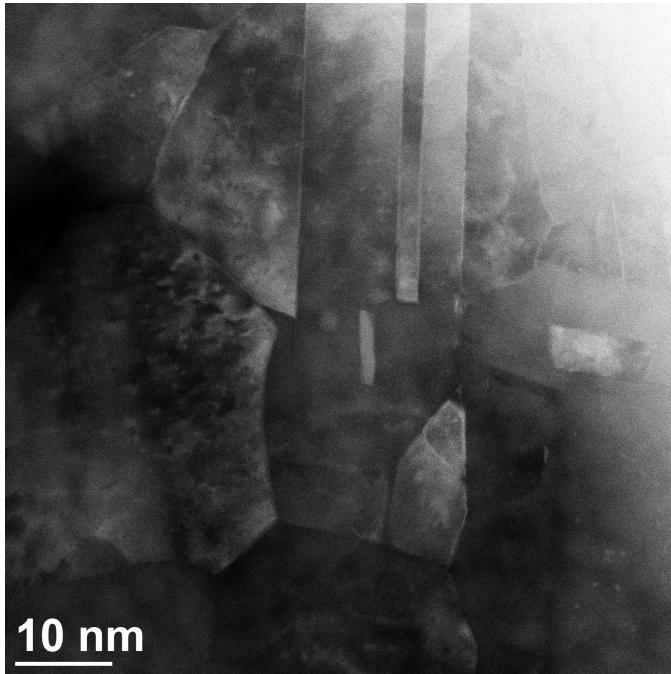
Miedema Model:

$$\Delta H_{\text{mix}}^{(50\% \text{Ni}-50\% \text{Bi})} = -3.7 \text{ kJ/mol}$$

$$\Delta H_{\text{mix}}^{(50\% \text{Cu}-50\% \text{Bi})} = +3.56 \text{ kJ/mol}$$

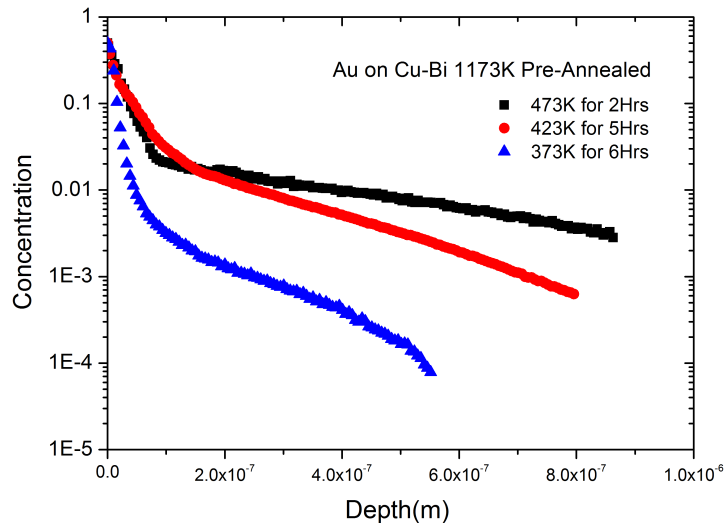
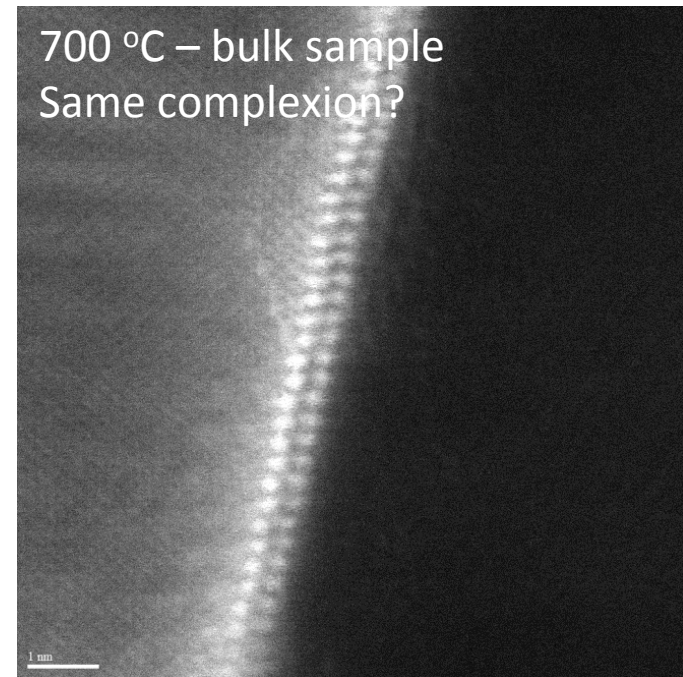
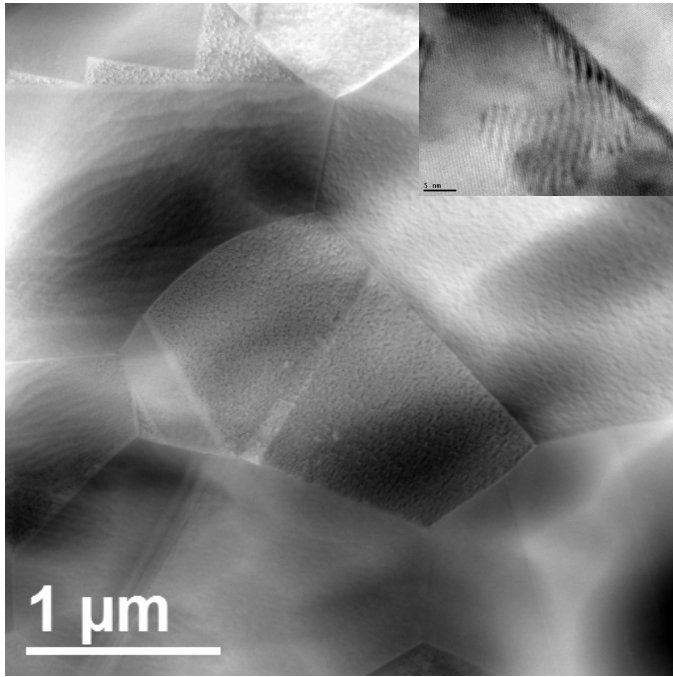


500 °C Pre-annealed with Bi



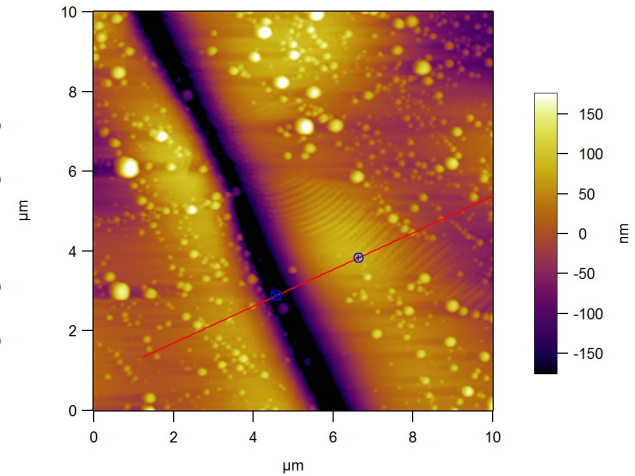
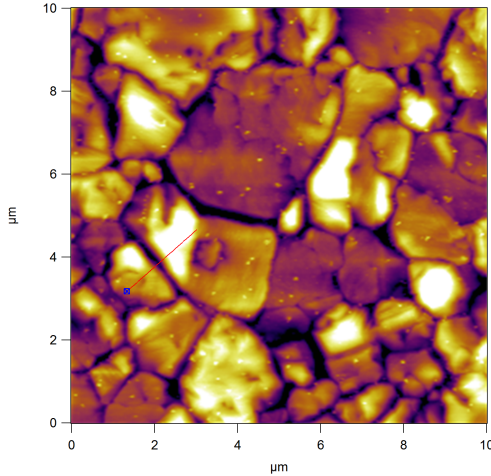
$$\bar{c}(z) \approx \bar{c}_{gb}(z) \propto \text{erfc} \left(\frac{z}{2\sqrt{D_{gb}t}} \right)$$

900 °C Pre-annealed with Bi



$$\bar{c}(z) \approx \bar{c}_{gb}(z) \propto \operatorname{erfc} \left(\frac{z}{2\sqrt{D_{gb}t}} \right)$$

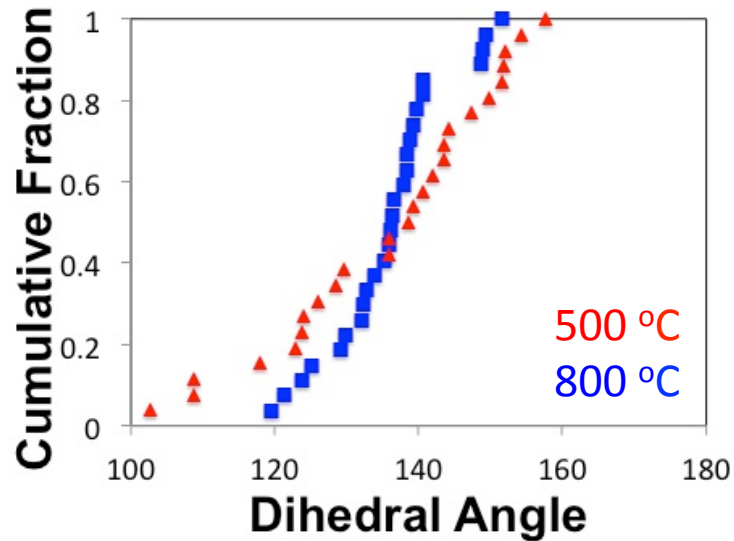
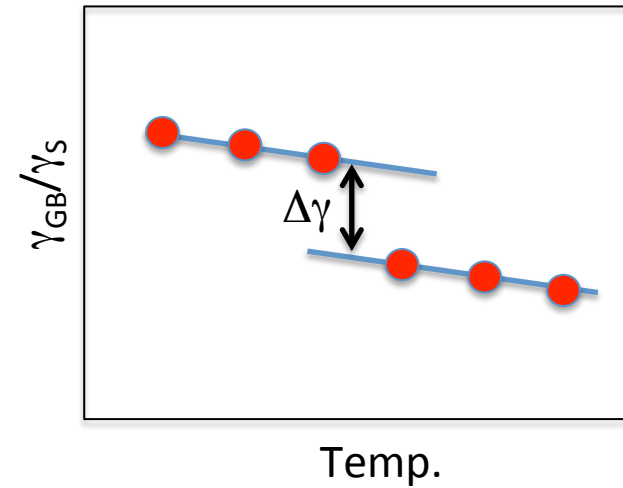
Preliminary Dihedral Analysis

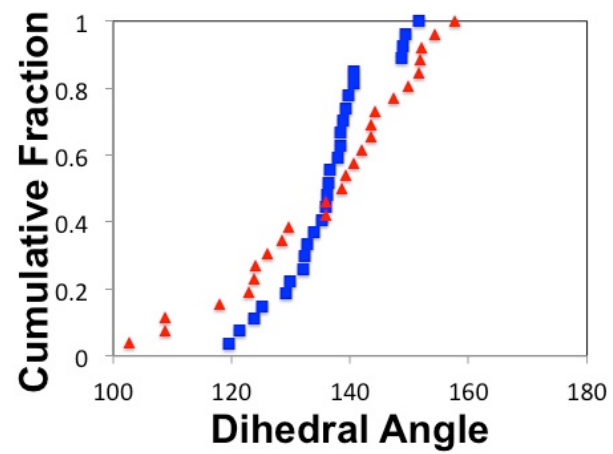
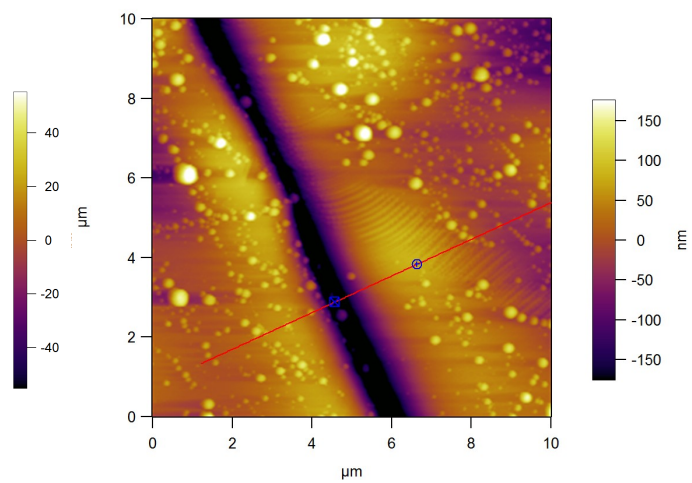
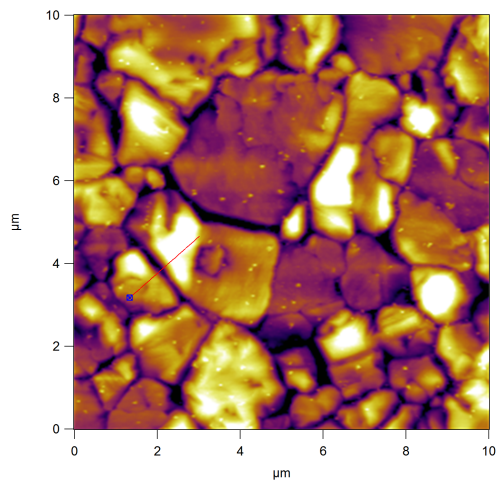


Measuring $\Delta\gamma$ for:

$$\Delta\gamma = \Delta\rho[-T(\Delta S_I - \Delta S_{II}) + (\Delta H_I - \Delta H_{II})]$$

Expected data:





Equations for Fitting Diffusion Data

Type B



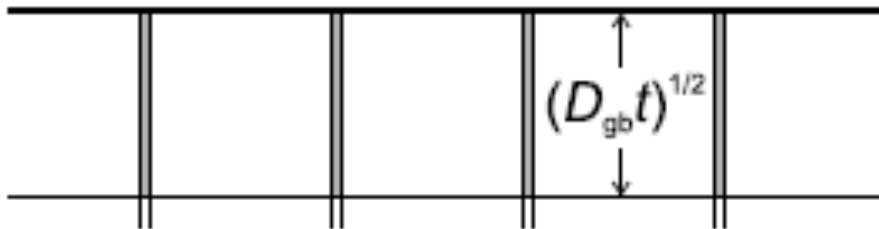
Instantaneous Source

$$sD_{gb}\delta = 1.322\sqrt{\frac{D}{t}}(-\partial\bar{c}/\partial z^{6/5})^{-5/3}$$

Constant Source

$$sD_{gb}\delta = 1.308\sqrt{\frac{D}{t}}(-\partial\bar{c}/\partial z^{6/5})^{-5/3}$$

Type C

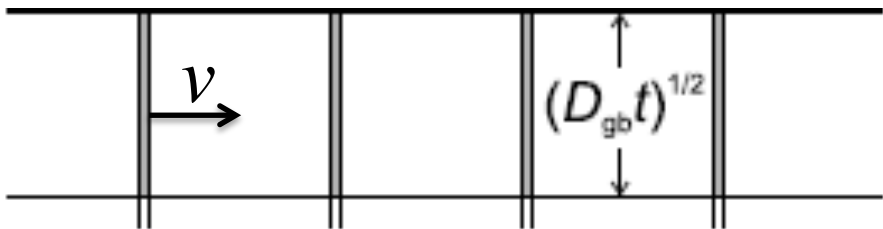


Instantaneous Source

$$\bar{c}(z) \approx \bar{c}_{gb}(z) \propto \exp\left(-\frac{z^2}{4D_{gb}t}\right)$$

Constant Source

$$\bar{c}(z) \approx \bar{c}_{gb}(z) \propto \operatorname{erfc}\left(\frac{z}{2\sqrt{D_{gb}t}}\right)$$



Mobile Grain Boundaries

$$\delta D_b = v\left(\frac{\partial \ln \bar{c}}{\partial z}\right)^{-2}$$